

comprising:

depositing a dielectric film over a semiconductor substrate; and

subjecting the dielectric film to a wet oxidation in a rapid thermal process chamber at a temperature greater than about 450 °C.

42. (new) A method of fabricating a semiconductor device, the method comprising:

depositing a dielectric film over a semiconductor substrate to form one of a gate and a capacitor dielectric; and

subjecting the dielectric film to a wet oxidation in a rapid thermal process chamber at a temperature greater than about 450 °C.

REPLACEMENT CLAIMS

Sub 01  
13. (amended) A method of fabricating a semiconductor device, the method comprising:

depositing a dielectric film over an active region of a semiconductor substrate to form part of a gate of a transistor; and

B2  
subjecting the dielectric film to a wet oxidation in a rapid thermal process chamber at a temperature greater than about 450 °C.

SUB G17  
18. (amended) A method of fabricating a semiconductor device, the method comprising:

B3  
depositing a dielectric film over an active region of a semiconductor substrate to form part of a gate of a transistor; and

providing steam to a vicinity of the dielectric film while the substrate is in a rapid thermal process chamber at a temperature greater than about 450 °C.